

	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 6149582 B1	2001/12/20	13	Small electrode for a chalcogenide switching device and method for fabricating same	257/3 ; 438/244 ; 438/95	Reinberg, Alan R. et al.	
2	US 6153890 A	2000/11/28	19	Memory cell incorporating a chalcogenide element	257/3	Wolstenholme, Graham R. et al.	
3	US 6031287 A	2000/02/29	24	Contact structure and memory element incorporating the same	257/734	Harshfield, Steven T.	
4	US 5751012 A	1998/05/12	13	Polysilicon pillar diode for use in a non-volatile memory cell	257/5 ; 257/4 ; 257/530 ; 365/163	Wolstenholme, Graham R. et al.	
5	US 4177475 A	1979/12/04	8	High temperature amorphous memory device for an electrically alterable read-only memory	257/2	Holmberg, Scott H.	
6	US 4115872 A	1978/09/19	7	Amorphous semiconductor memory device for employment in an electrically alterable read-only memory	365/163	Bluhm, Vernon A.	

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